

PLASTIC SILICON RECTIFIER

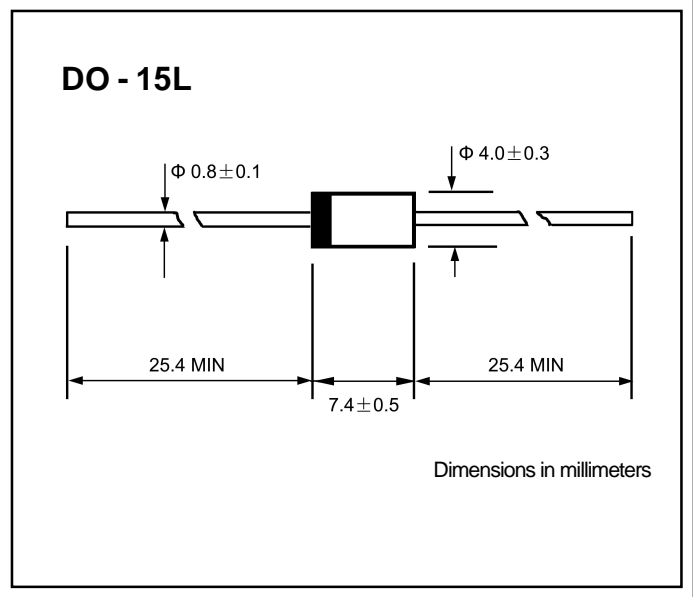
VOLTAGE RANGE: 200 --- 1000 V
CURRENT: 1.2 A

FEATURES

- ◇ Low cost
- ◇ Diffused junction
- ◇ Low leakage
- ◇ Low forward voltage drop
- ◇ High current capability
- ◇ Easily cleaned with Freon, Alcohol, Isopropanol and similar solvents
- ◇ The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- ◇ Case: JEDEC DO--15L, molded plastic
- ◇ Terminals: Axial lead, solderable per MIL-STD-202, Method 208
- ◇ Polarity: Color band denotes cathode
- ◇ Weight: 0.017 ounces, 0.48 grams
- ◇ Mounting position: Any



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

		RM2Z	RM2	RM2A	RM2B	RM2C	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	200	400	600	800	1000	V
Maximum average forward rectified current 9.5mm lead lengths, @ $T_A=75^\circ C$	$I_{(AV)}$	1.2					A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load @ $T_j=125^\circ C$	I_{FSM}	100					A
Maximum instantaneous forward voltage at 1.2 A	V_F	0.91					V
Maximum reverse current @ $T_A=25^\circ C$ at rated DC blocking voltage @ $T_A=100^\circ C$	I_R	10.0 50					μA
Typical junction capacitance (Note1)	C_J	30					pF
Typical thermal resistance (Note2)	$R_{\theta jA}$	50					$^\circ C/W$
Operating junction temperature range	T_j	- 55 ---- + 150					$^\circ C$
Storage temperature range	T_{STG}	- 55 ---- + 150					$^\circ C$

NOTE: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

2. Thermal resistance from junction to ambient.

FIG.1 – FORWARD DERATING CURVE

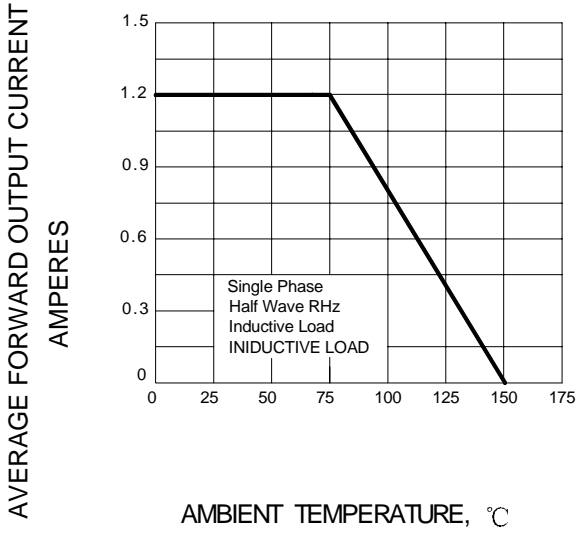


FIG.2 – PEAK FORWARD SURGE CURRENT

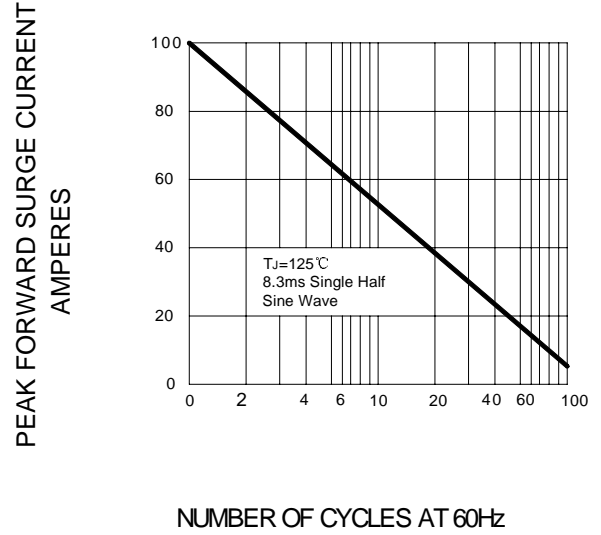


FIG.3 – TYPICAL FORWARD CHARACTERISTIC

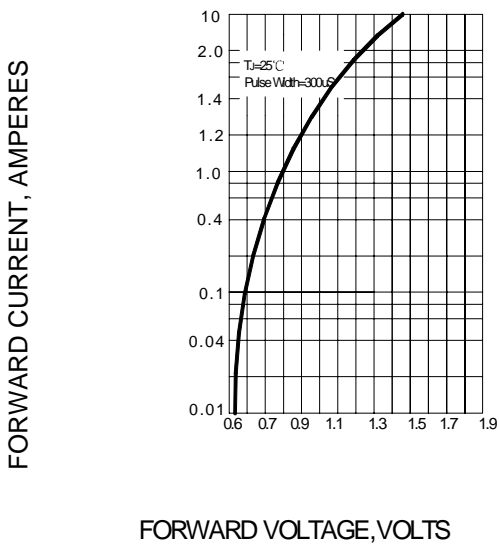


FIG.4 – TYPICAL REVERSE CHARACTERISTICS

